Curriculum vitae

PERSONAL INFORMATION	
First Name, Surname	Oleg Olikh
Date of Birth	1974-06-05
Citizenship	Ukraine
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EDUCATION	
1996-2000	Post-graduate course at the general physics department in Taras Shevchenko National University of Kyiv
1991-1996	Physics faculty of Taras Shevchenko University of Kyiv, master in solid state physics (diploma ЛТ ВЕ №001760, 28.06.1996)
ACADEMIC DEGREE, ACADEMIC RANK	
2018	Doctor of Science Degree (Dr. Hab. , Physics and Mathematics), solid state physics specialty, thesis «Acoustically and radiation induced phenomena in surface barrier silicon and gallium arsenide structures»
2004	Academic rank of associate professor at the general physics department
2001	PhD Degree (Physics and Mathematics), solid state physics specialty, thesis «Investigation of acousto-photo-electric interaction in GaAs and Si semiconductor structures»
WORK EXPERIENCE	
2021 - Present	Professor at the general physics department, Taras Shevchenko National University of Kyiv, Kyiv (Ukraine)
2002 - 2021	Associate professor at the general physics department, Taras Shevchenko National University of Kyiv, Kyiv (Ukraine)
1998-2002	Assistant at the general physics department Taras Shevchenko National University of Kyiv, Kyiv (Ukraine)
AWARDS AND HONORS	
2021	I. Puluj Prize of the National Academy of Sciences of Ukraine
LANGUAGES	Ukrainian - C2, Russian – C2, English – B2.
SCIENTIFIC ACTIVITY	
Number of Scientific Papers	86
Main Stream of Research	Field of knowledge "Nature Sciences" - the ultrasound effect on materials; - using of ultrasound methods to determine the semiconductor structure parameters; acousto-stimulated dynamic phenomena in semiconductor barrier structures
Papers in Q1 and Q2 Journals (2013–2022)	1. Olikh O., Lytvyn P. «Defect engineering using microwave processing in SiC and GaAs», Semiconductor Science and Technology, 2022, vol.37, is.7, 075006, https://doi.org/10.1088/1361-6641/ac6f17 2. Olikh O., Kostylyov V., Vlasiuk V., Korkishko R., Chupryna R. «Intensification of iron–boron complex association in silicon solar cells under acoustic wave action», Journal of Materials Science: Materials in Electronics, 2022, vol.33, is.13, P. 13133-13142, https://doi.org/10.1007/s10854-022-08252-3

3. Olikh O., Lozitsky O., Zavhorodnii O. «Estimation for iron contamination in Si solar cell by ideality factor: Deep neural network approach», Progress in Photovoltaics: Research and Applications, 2022, vol.30, is.6, p. 648-660; https://doi.org/10.1002/pip.3539
4. Olikh O., Kostylyov V., Vlasiuk V., Korkishko R., Olikh Ya., Chupryna R. «Features of FeB pair light-induced dissociation and repair in silicon *n*+-*p*-*p*+ structures under ultrasound loading», Journal of Applied Physics, 2021, vol.130, is.23, 235703; https://doi.org/10.1063/5.0073135
5. Olikh Ya. M., Tymochko M. D., Olikh O.Ya. «Mechanisms of two-stage conductivity relaxation in CdTe:Cl with ultrasound», Journal of Electronic Materials, 2020, vol.49, is.8, P. 4524-4530; https://doi.org/10.1007/s11664-020-08179-7
6. Gorb A.M., Korotchenkov O.A., Olikh O.Ya., Podolian A.O., Chupryna R.G. «Influence of γ-irradiation and ultrasound treatment on current mechanism in Au-SiO_2-Si structure», Solid State Electronics, 2020, vol.165, 107712; https://doi.org/10.1016/j.sse.2019.107712
7. Olikh O.Ya. «Relationship between the ideality factor and the iron concentration in silicon solar cells», Superlattices and Microstructures, 2019, vol.136, 106309; https://doi.org/10.1016/j.spmi.2019.106309
8. Olikh Ya. M., Tymochko M. D., Olikh O.Ya., Shenderovsky V. A. «Clusters of point defects near dislocations as a tool to control CdZnTe electrical parameters by ultrasound», Journal of Electronic Materials, 2018, vol.47, is.8, P. 4370-4378; https://doi.org/10.1007/s11664-018-6332-4
9. Olikh O.Ya. «Acoustically driven degradation in single crystalline silicon solar cell», Superlattices and Microstructures, 2018, vol.117, p. 173-188; https://doi.org/10.1016/j.spmi.2018.03.027
10. Olikh O.Ya., Gorb A.M., Chupryna R.G., Pristay-Fenenkov O.V. «Acousto-defect interaction in irradiated and non-irradiated silicon n^+–p structures», Journal of Applied Physics, 2018, vol.123, is.16, 161573; https://doi.org/10.1063/1.5001123
11. Olikh O.Ya., Voytenko K.V. «On the mechanism of ultrasonic loading effect in silicon-based Schottky diodes», Ultrasonics, 2016, vol.66, p. 1-3; https://doi.org/10.1016/j.ultras.2015.12.001
12. Olikh O.Ya. «Review and test of methods for determination of the Schottky diode parameters», Journal of Applied Physics, 2015, vol.118, is.2, 024502; https://doi.org/10.1063/1.4926420
13. Olikh O.Ya., Voytenko K.V., Burbelo R.M. «Ultrasound influence on I–V–T characteristics of silicon Schottky barrier structure», Journal of Applied Physics, 2015, vol.117, is.4, 044505; https://doi.org/10.1063/1.4906844
14. Olikh O.Ya. «Reversible influence of ultrasound on *γ*-irradiated Mo/*n*-Si Schottky barrier structure», Ultrasonics, 2015, vol.56, p. 545-550; https://doi.org/10.1016/j.ultras.2014.10.008
15. Olikh O.Ya. «Non-Monotonic γ-Ray Influence on Mo/n-Si Schottky Barrier Structure Properties», IEEE Transactions on Nuclear Science, 2013, vol.60, is.1, part 2, p.394-401; https://doi.org/10.1109/TNS.2012.2234137